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## LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.: P68972US0 GROUP ART UNIT: Not Yet Assigned  
SERIAL NO.: New Application FILING DATE: July 9, 2003  
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## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	INT'L CLASS	SUB- CLASS	FILING DATE (if appropriate)
AA						
AB						

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## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION (YES) (NO)
AC						
AD						

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## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

LP AE C.H.Chen, et al; "Thermally-Enhanced Remote Plasma Nitrided Ultrathin (1.65nm) Gate Oxide with Excellent Performances in Reduction of Leakage Current and Boron Diffusion"; IEEE Electron Device Letters, Vol.22, No. 8; August 2001; pp.378-380.

AF Hoon Lim, et al; "The Effects of STI Process Parameters on the Integrity of Dual Gate Oxides"; IEEE 01CH37167 39th Annual International Reliability Physics Symposium, 2001; pp. 48-51.

✓ AG S.Song, et al; "On the Gate Oxide Scaling of High Performance CMOS Transistors"; 2001 IEEE; IEDM 01-55 to IEDM 01-58.

EXAMINER

DATE CONSIDERED

Long Pham3/29/04

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).